TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

T C 7 M H 3 7 3 F K

Octal D-Type Latch with 3-State Output

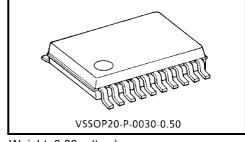
The TC7MH373FK is an advanced high speed CMOS octal latch with 3-state output fabricated with silicon gate $\rm C^2MOS$ technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while marinating the CMOS low power dissipation.

This 8 bit D-type latch is controlled by a latch enable input (LE) and a output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures the 0 to 7 V can be applied



Weight: 0.03 g (typ.)

to the input pins can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents destruction due to mismatched supply and input voltages.

Features

- High speed: $t_{pd} = 5.0 \text{ ns (typ.) (VCC} = 5 \text{ V)}$
- Low power dissipation: $ICC = 4 \mu A \text{ (max) (Ta} = 25 \text{°C)}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: t_pLH ≃ t_pHL
- Wide operating voltage range: VCC (opr) = 2~5.5 V
- Low noise: VOLP = 0.8 (max)
- Pin and function compatible with 74ALS373

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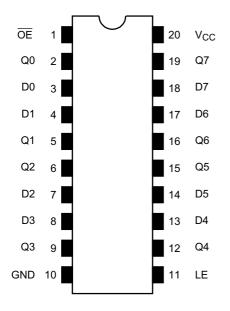
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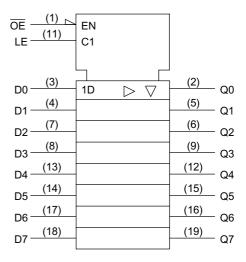
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Pin Assignment (top view)



IEC Logic Symbol



Truth Table

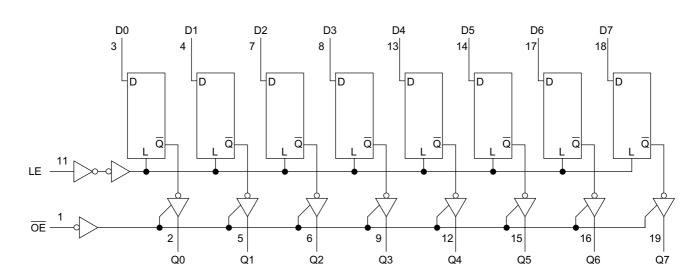
	Outputs		
ŌĒ	LE	D	Outputs
Н	Х	Х	Z
L	L	Х	Q _n
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

 Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	I _{CC}	±75	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	V _{OUT}	0~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100 \ (V_{CC}=3.3\pm0.3 \ V)$	ns/V
input rise and rail unie	ui/uv	$0\sim20 \ (V_{CC}=5\pm0.5 \ V)$	115/V



Electrical Characteristics

DC Characteristics

Characteristics		Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Cilarac	tensucs	Symbol			V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
			_		2.0	1.50	_	_	1.50	_	
Input voltage	High level	V_{IH}			3.0~5.5	V _{CC} ×0.7			V _{CC} ×0.7		V
input voltage					2.0	_	_	0.50	_	0.50	v
	Low level	V_{IL}	_		3.0~5.5	1	1	$\begin{array}{c} V_{CC} \\ \times 0.3 \end{array}$	_	$\begin{array}{c} V_{CC} \\ \times 0.3 \end{array}$	
					2.0	1.9	2.0	_	1.9		
			., .,	$I_{OH} = -50 \mu A$	3.0	2.9	3.0	_	2.9	_	
Output	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}		4.5	4.4	4.5	_	4.4	_	V
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	_	
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	_	
voltage					2.0	_	0	0.1	_	0.1	v
				$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1	
	Low level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}		4.5	_	0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
			$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44		
3-state output	off-state current	l _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_	_	±0.25	_	±2.50	μΑ
Input leakage	current	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μΑ
Quiescent sup	ply current	Icc	$V_{IN} = V_{CC}$ or GND		5.5			4.0		40.0	μΑ



Timing Requirements (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Cumbal	Test Condition		Ta = 25°C		Ta = -40~85°C	Unit	
Characteristics	Symbol Test Condition		V _{CC} (V)	Тур.	Limit	Limit	Offic	
Minimum pulse width	+		3.3 ± 0.3	_	5.0	5.0	no	
(LE)	t _{w (H)}		5.0 ± 0.5		5.0	5.0	ns	
Minimum set un time	ts		3.3 ± 0.3		4.0	4.0	ns	
Minimum set-up time			5.0 ± 0.5		4.0	4.0	115	
Minimum hold time	+.		3.3 ± 0.3		1.0	1.0	ns	
	t _h	_	5.0 ± 0.5	_	1.0	1.0	110	

AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -4	Unit	
Characteristics	Symbol	Test Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
			3.3 ± 0.3	15	_	7.0	11.0	1.0	13.0	ns
Propagation delay time	t _{pLH}		3.3 ± 0.3	50	_	9.5	14.5	1.0	16.5	
(LE-Q)	t _{pHL}	_	5.0 ± 0.5	15	_	4.9	7.2	1.0	8.5	115
			3.0 ± 0.3	50	_	6.4	9.2	1.0	10.5	
			3.3 ± 0.3	15	_	7.3	11.4	1.0	13.5	
Propagation delay time	t _{pLH}		3.3 ± 0.3	50	_	9.8	14.9	1.0	17.0	20
(D-Q)	t _{pHL}	_	5.0 ± 0.5	15	_	5.0	7.2	1.0	8.5	ns
			3.0 ± 0.3	50	_	6.5	9.2	1.0	10.5	
	t _{pZL} t _{pZH}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15	_	7.3	11.4	1.0	13.5	- ns
3-state output enable time				50	_	9.8	14.9	1.0	17.0	
3-state output enable time			5.0 ± 0.5	15		5.5	8.1	1.0	9.5	
				50	_	7.0	10.1	1.0	11.5	
3-state output disable time	t_{pLZ}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	50	_	9.5	13.2	1.0	15.0	ns
3-state output disable time	t_{pHZ}	N_	5.0 ± 0.5	50	_	6.5	9.2	1.0	10.5	115
Output to output skew	t _{osLH}	(Note1)	3.3 ± 0.3	50	_	_	1.5	_	1.5	ns
Output to output skew	t _{osHL}	(Note I)	5.0 ± 0.5	50	_	_	1.0	_	1.0	115
Input capacitance	C _{IN}		_		_	4	10	_	10	pF
Bus input capacitance	C _{OUT}	-	_		_	6	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note2)	_	27	_	_	_	pF

Note1: This parameter is guaranteed by design.

 $t_{OSLH} = |t_{DLHm} - t_{DLHn}|, t_{OSHL} = |t_{DHLm} - t_{DHLn}|$

Note2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC \text{ (opr)}} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per latch)}$

And the total CPD when n pcs of latch operate can be gained by the following equation:

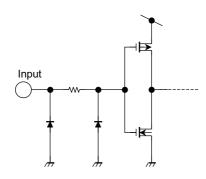
 C_{PD} (total) = 14 + 13• n



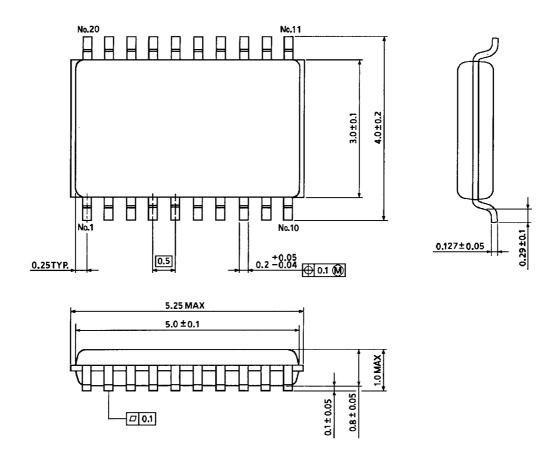
Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		- Unit
Gilalacteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.5	8.0	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.5	-0.8	V
Minimum high level dynamic input voltage V_{IH}	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

Input Equivalent Circuit



Package Dimensions



Weight: 0.03 g (typ.)